TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK3078

900 MHz BAND AMPLIFIER APPLICATIONS (GSM)

- **Output** Power
- $: P_{O} = 27.0 \text{ dBmW}$ (Min.)
- Gain

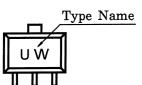
- $: G_P = 12.5 dB (Min.)$
- Drain Efficiency
 - $: \eta p = 46\%$ (Typ.)

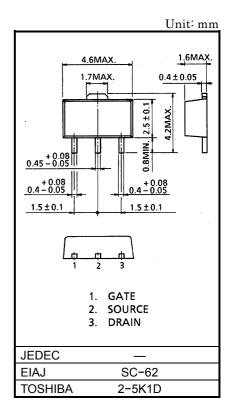
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V _{DSS}	10	V
Gate-Source Voltage	V _{GSS}	5	V
Drain Current	I _D	0.5	А
Power Dissipation	P _{D*}	3.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature Range	T _{stg}	-45~150	°C

*: Tc = 25°C When mounted on a 1.6 mm glass epoxy PCB

MARKING





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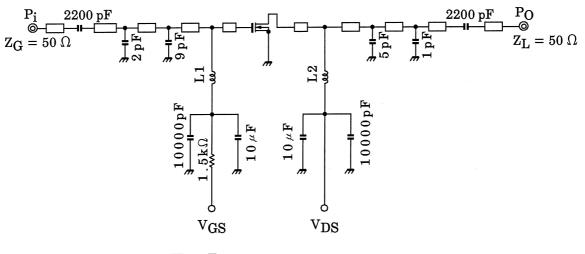
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Output Power	PO	$V_{DS} = 4.8 V$	27.0	_	_	dBmW
Drain Efficiency	η _D	lidle = 108 mA (V _{GS} = adjust) f = 915 MHz, P _i = 14.5 dBmW	-	46.0	_	%
Power Gain	GP	$Z_G = Z_L = 50 \Omega$	12.5	_	_	dB
Threshold Voltage	V _{th}	V _{DS} = 4.8 V, I _D = 0.5 mA	0.20	_	1.20	V
Drain Cut-off Current	I _{DSS}	V _{DS} = 10 V, V _{GS} = 0 V	_	_	10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = 5 V, V _{DS} = 0 V	_	_	5	μA

CAUTION

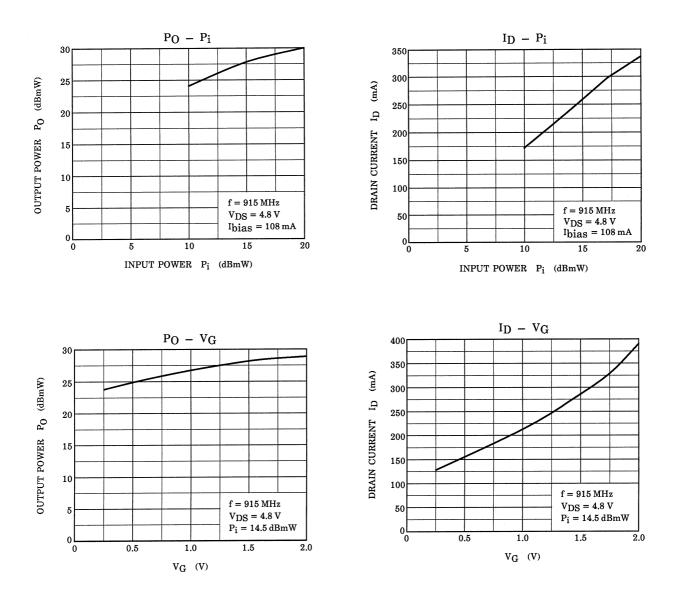
This transistor is the electrostatic sensitive device. Please handle with caution.

RF OUTPUT POWER TEST FIXTURE



L1 : $\phi 0.6 \text{ mm}$, 5.5 mmID, 4T L2 : $\phi 0.6 \text{ mm}$, 5.5 mmID, 8T

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CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.